

Listing of Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. Cancelled
2. Cancelled
3. Cancelled
4. (Currently amended) The method according to claim 13 wherein steps a)-~~d~~) b) are performed at pressures of 0.1 Bar or higher.
5. Cancelled
6. Cancelled
7. Cancelled
8. Cancelled
9. Cancelled
10. Cancelled
11. (Currently amended) The method according to claim ~~9~~ 13 further including the step of performing a post-deposition etch to remove fluorocarbon residue from areas where its presence is undesirable.
12. Cancelled
13. (New) In a method of making an electronic device in which a conductive electrode has been formed over a substrate, comprising:
 - a) providing an oxidizing plasma in a processing station to modify the properties of the conductive electrode by using shaped and appropriately positioned plasma producing electrodes to produce the oxygen-containing plasma in the processing station; and
 - b) producing a fluorocarbon plasma in the processing station to form a fluorocarbon layer over the modified conductive electrode and using the shaped electrodes to produce a spatially modulated fluorocarbon plasma in the chamber, which forms a fluorocarbon layer in selected areas of the substrate electrode structure including over the substrate electrode structure..
14. (New) The method of claim 13 wherein the conductive electrode is ITO.
15. (New) In a method of making an electronic device in which a conductive electrode has been formed over a substrate, comprising:

a) providing an oxidizing plasma in a processing station to modify the properties of the conductive electrode by using appropriately positioned plasma producing electrodes to produce the oxygen-containing plasma in the processing station; and

b) producing a fluorocarbon plasma in the processing station to form a fluorocarbon layer over the modified conductive electrode by selecting a mixture of gases including a fluorine containing gas which will cause a thicker deposition of the fluorocarbon layer over the electrode than regions adjacent to the electrodes.

16. (New) The method according to claim 15 wherein the mixture of gases is at least one fluorocarbon gas which does not contain hydrogen, a noble gas, and a hydrogen containing gas.

17. (New) The method of claim 16 wherein the gas mixtures contain CF_4 , helium and CHF_3 .

18. (New) The method of claim 15 wherein the electrode is ITO.